

BIAS-INDEPENDENT CAPACITOR BASED ON SUPERPOSITION OF
NONLINEAR CAPACITORS FOR ANALOG/RF CIRCUIT APPLICATIONS

ABSTRACT OF THE DISCLOSURE

A first MOS-on-NWELL device is formed on a substrate and has its pickup terminals optionally connected together. A second MOS-on-NWELL device is formed on the substrate and has its pickup terminals optionally connected together. A gate of the first MOS-on-NWELL device is connected to the pickup terminals of the second MOS-on-NWELL device. A gate of the second MOS-on-NWELL device is connected to the pickup terminals of the first MOS-on-NWELL device. A first PMOS transistor is formed on a substrate and has its source and drain terminals connected together. A second PMOS transistor is formed on a substrate and has its source and drain terminals connected together. A gate of the first PMOS transistor is connected to the source and drain terminals of the second PMOS transistor. A gate of the second PMOS transistor is connected to the source and drain terminals of the first PMOS transistor. A combination of the first and second PMOS transistors are connected in parallel with the first and second MOS-on-NWELL devices.

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